Preferred Device

General Purpose Transistor

PNP Silicon

Features

• Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-40	Vdc
Collector - Base Voltage	V _{CBO}	-40	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ic	-200	mAdc

THERMAL CHARACTERISTICS

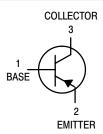
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C	P_{D}	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C	P_{D}	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	ç

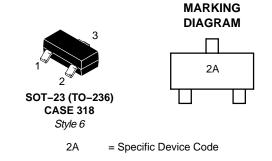
- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



ON Semiconductor®

http://onsemi.com





ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT3906LT1	SOT-23	3000 / Tape & Reel
MMBT3906LT1G	SOT-23	3000 / Tape & Reel
MMBT3906LT3	SOT-23	10000 / Tape & Reel
MMBT3906LT3G	SOT-23	10000 / Tape & Reel

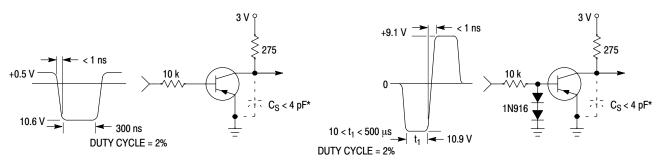
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Charac	teristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		1	1	ı	<u> </u>
Collector – Emitter Breakdown Voltage (I _C =	$-1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	-40	_	Vdc
Collector – Base Breakdown Voltage (I _C = –10 μAdc, I _E = 0)			-40	_	Vdc
Emitter-Base Breakdown Voltage (I _E = -10	μ Adc, I _C = 0)	V _{(BR)EBO}	-5.0	_	Vdc
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB} =	-3.0 Vdc)	I _{BL}		-50	nAdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB} = -3.0 Vdc)				-50	nAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain $ \begin{aligned} &(I_C = -0.1 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ &(I_C = -1.0 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ &(I_C = -10 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ &(I_C = -50 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \\ &(I_C = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}) \end{aligned} $		H _{FE}	60 80 100 60 30	 300 	
Collector – Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -1.0$ mAdc) ($I_C = -50$ mAdc, $I_B = -5.0$ mAdc)		V _{CE(sat)}	_ _	-0.25 -0.4	Vdc
Base – Emitter Saturation Voltage (I_C = -10 mAdc, I_B = -1.0 mAdc) (I_C = -50 mAdc, I_B = -5.0 mAdc)		V _{BE(sat)}	-0.65 —	-0.85 -0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS	5				
Current – Gain — Bandwidth Product ($I_C = -$	$-10 \text{ mAdc}, V_{CE} = -20 \text{ Vdc}, f = 100 \text{ MHz}$	f _T	250	_	MHz
Output Capacitance ($V_{CB} = -5.0 \text{ Vdc}$, $I_E = 0$), f = 1.0 MHz)	C _{obo}	1	4.5	pF
Input Capacitance (V _{EB} = -0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	-	10	pF
Input Impedance (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1.0 kHz)		h _{ie}	2.0	12	kΩ
Voltage Feedback Ratio (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1.0 kHz)		h _{re}	0.1	10	X 10 ⁻⁴
Small – Signal Current Gain (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1.0 kHz)		h _{fe}	100	400	_
Output Admittance (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1.0 kHz)		h _{oe}	3.0	60	μmhos
Noise Figure (I _C = $-100 \mu\text{Adc}$, V _{CE} = -5.0Vdc , R _S = $1.0 \text{k}\Omega$, f = 1.0kHz)		NF	_	4.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	$(V_{CC} = -3.0 \text{ Vdc}, V_{BE} = 0.5 \text{ Vdc},$	t _d	_	35	200
Rise Time	$I_C = -10 \text{ mAdc}, I_{B1} = -1.0 \text{ mAdc})$	t _r	_	35	ns
Storage Time	$(V_{CC} = -3.0 \text{ Vdc}, I_{C} = -10 \text{ mAdc},$	t _s		225	ns
Fall Time	$I_{B1} = I_{B2} = -1.0 \text{ mAdc}$	t _f	_	75	113

3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



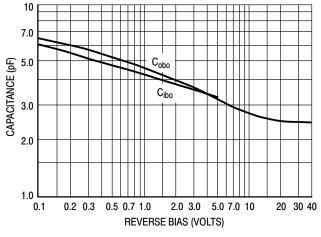
^{*} Total shunt capacitance of test jig and connectors

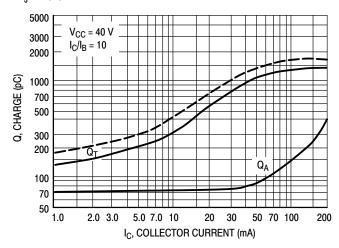
Figure 1. Delay and Rise Time Equivalent Test Circuit

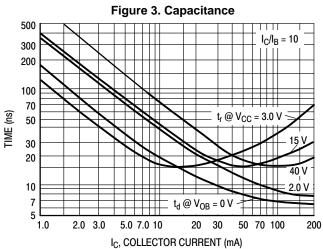
Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

T_J = 25°C
T_J = 125°C







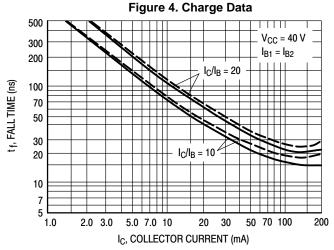
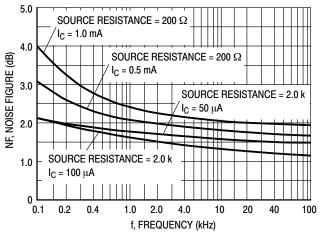


Figure 5. Turn-On Time

Figure 6. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



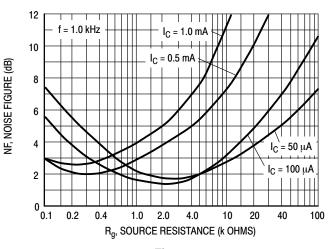
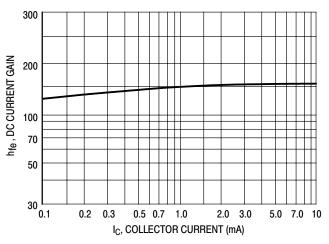


Figure 7.

Figure 8.

h PARAMETERS

 $(V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C})$



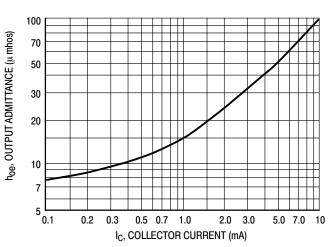
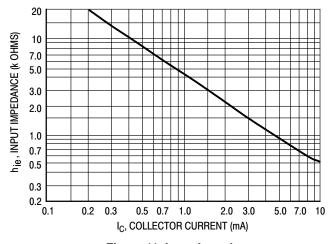


Figure 9. Current Gain

Figure 10. Output Admittance



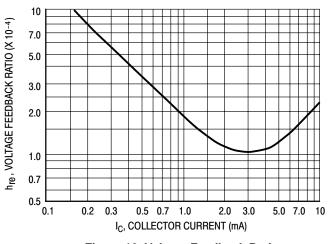


Figure 11. Input Impedance

Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

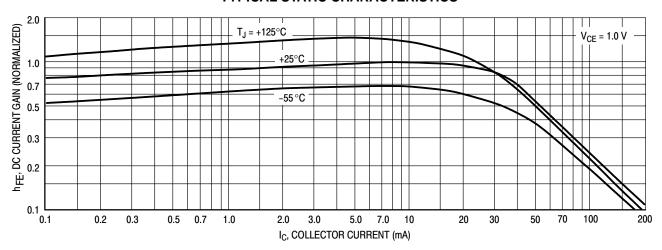


Figure 13. DC Current Gain

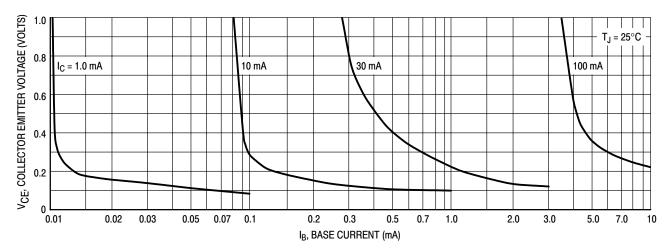


Figure 14. Collector Saturation Region

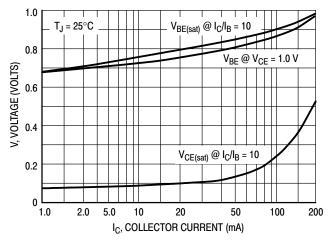


Figure 15. "ON" Voltages

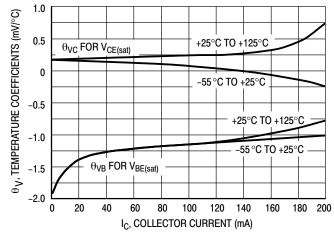


Figure 16. Temperature Coefficients

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AH**

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTROLLING DIMENSION, INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08

	INC	CHES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
7	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
٧	0.0177	0.0236	0.45	0.60

STYLE 6:

- PIN 1. BASE
- 2 **EMITTER**
- COLLECTOR 3.

SOLDERING FOOTPRINT*

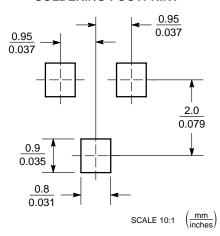


Figure 17. SOT-23

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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